

ABSTRACT OF THE DISCLOSURE

Provide is a 3-5 group compound semiconductor having a concentration of a p-type dopant of $1 \times 10^{17} \text{ cm}^{-3}$ or more and $1 \times 10^{21} \text{ cm}^{-3}$ or less, which can be laminated to control the carrier concentration of an InGaAlN-type mixed crystal in a low range with high reproducibility. Also provided is a 3-5 group compound semiconductor in which the carrier concentration of an InGaAlN-type mixed crystal is controlled in a low range with high reproducibility, and a light emitting device having high light emitting efficiency.

09387660-1-1501